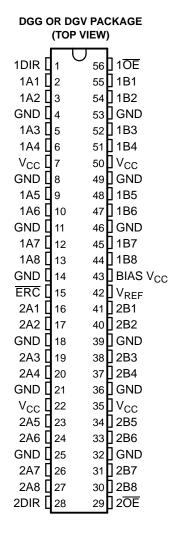
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FEATURES

- Member of the Texas Instruments Widebus™
 Family
- TI-OPC™ Circuitry Limits Ringing on Unevenly Loaded Backplanes
- OEC[™] Circuitry Improves Signal Integrity and Reduces Electromagnetic Interference
- Bidirectional Interface Between GTLP Signal Levels and LVTTL Logic Levels
- LVTTL Interfaces Are 5-V Tolerant
- High-Drive GTLP Outputs (100 mA)
- LVTTL Outputs (-24 mA/24 mA)
- Variable Edge-Rate Control (ERC) Input Selects GTLP Rise and Fall Times for Optimal Data-Transfer Rate and Signal Integrity in Distributed Loads
- I_{off}, Power-Up 3-State, and BIAS V_{CC} Support Live Insertion
- Bus Hold on A-Port Data Inputs
- Distributed V_{CC} and GND Pins Minimize High-Speed Switching Noise
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II



DESCRIPTION/ORDERING INFORMATION

The SN74GTLPH1645 is a high-drive, 16-bit bus transceiver that provides LVTTL-to-GTLP and GTLP-to-LVTTL signal-level translation. It is partitioned as two 8-bit transceivers. The device provides a high-speed interface between cards operating at LVTTL logic levels and a backplane operating at GTLP signal levels. High-speed (about three times faster than standard LVTTL or TTL) backplane operation is a direct result of GTLP's reduced output swing (<1 V), reduced input threshold levels, improved differential input, OECTM circuitry, and TI-OPCTM circuitry. Improved GTLP OEC and TI-OPC circuits minimize bus-settling time and have been designed and tested using several backplane models. The high drive allows incident-wave switching in heavily loaded backplanes with equivalent load impedance down to 11 Ω.

GTLP is the Texas Instruments derivative of the Gunning Transceiver Logic (GTL) JEDEC standard JESD 8-3. The ac specification of the SN74GTLPH1645 is given only at the preferred higher noise-margin GTLP, but the user has the flexibility of using this device at either GTL ($V_{TT} = 1.2 \text{ V}$ and $V_{REF} = 0.8 \text{ V}$) or GTLP ($V_{TT} = 1.5 \text{ V}$ and $V_{REF} = 1 \text{ V}$) signal levels.

Normally, the B port operates at GTLP signal levels. The A-port and control inputs operate at LVTTL logic levels, but are 5-V tolerant and are compatible with TTL and 5-V CMOS inputs. V_{REF} is the B-port differential input reference voltage.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

TEXAS INSTRUMENTS www.ti.com

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DESCRIPTION/ORDERING INFORMATION (CONTINUED)

This device is fully specified for live-insertion applications using I_{off} , power-up 3-state, and BIAS V_{CC} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict. The BIAS V_{CC} circuitry precharges and preconditions the B-port input/output connections, preventing disturbance of active data on the backplane during card insertion or removal, and permits true live-insertion capability.

This GTLP device features TI-OPC circuitry, which actively limits the overshoot caused by improperly terminated backplanes, unevenly distributed cards, or empty slots during low-to-high signal transitions. This improves signal integrity, which allows adequate noise margin to be maintained at higher frequencies.

High-drive GTLP backplane interface devices feature adjustable edge-rate control ($\overline{\text{ERC}}$). Changing the $\overline{\text{ERC}}$ input voltage between GND and V_{CC} adjusts the B-port output rise and fall times. This allows the designer to optimize system data-transfer rate and signal integrity to the backplane load.

Active bus-hold circuitry holds unused or undriven LVTTL data inputs at a valid logic state. Use of pullup or pulldown resistors with the bus-hold circuitry is not recommended.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, the output-enable (\overline{OE}) input should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

ORDERING INFORMATION

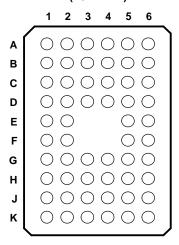
T _A	PACK	AGE ⁽¹⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	TSSOP - DGG	Tape and reel	SN74GTLPH1645DGGR	GTLPH1645
–40°C to 85°C	TVSOP - DGV	Tape and reel	SN74GTLPH1645DGVR	GL45
	VFBGA – GQL	Tape and reel	SN74GTLPH1645GQLR	GL45

⁽¹⁾ Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



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GQL PACKAGE (TOP VIEW)



TERMINAL ASSIGNMENTS

	1	2	3	4	5	6
Α	1A2	1A1	1DIR	1 OE	1B1	1B2
В	1A4	1A3	GND	GND	1B3	1B4
С	1A5	GND	V _{CC}	V _{CC}	GND	1B5
D	1A7	1A6	GND	GND	1B6	1B7
E	GND	1A8			1B8	BIAS V _{CC}
F	ERC	2A1			2B1	V_{REF}
G	2A2	2A3	GND	GND	2B3	2B2
Н	2A4	GND	V_{CC}	V_{CC}	GND	2B4
J	2A5	2A6	GND	GND	2B6	2B5
K	2A7	2A8	2DIR	2 OE	2B8	2B7

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FUNCTIONAL DESCRIPTION

The SN74GTLPH1645 is a high-drive (100-mA), 16-bit bus transceiver partitioned as two 8-bit segments and is designed for asynchronous communication between data buses. The device transmits data from the A port to the B port or from the B port to the A port, depending on the logic level at the direction-control (DIR) input. $\overline{\text{OE}}$ can be used to disable the device so the buses are effectively isolated. Data polarity is noninverting.

For A-to-B data flow, when \overline{OE} is low and DIR is high, the B outputs take on the logic value of the A inputs. When \overline{OE} is high, the outputs are in the high-impedance state.

The data flow for B to A is similar to A to B, except \overline{OE} and DIR are low.

FUNCTION TABLES

OUTPUT CONTROL

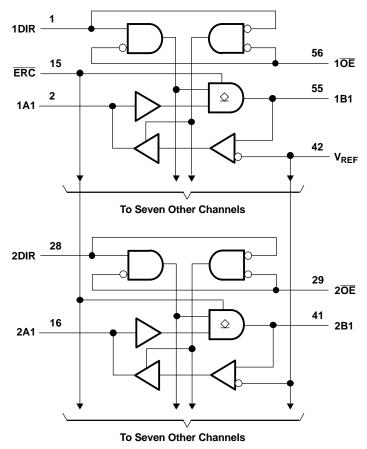
INP	UTS	OUTPUT	MODE				
ŌĒ	DIR	OUTFUT	MODE				
Н	Χ	Z	Isolation				
L	L	B data to A port	True transparent				
L	Н	A data to B port	True transparent				

B-PORT EDGE-RATE CONTROL (ERC)

INPU	T ERC	OUTPUT
LOGIC LEVEL	NOMINAL VOLTAGE	B-PORT EDGE RATE
L	GND	Slow
Н	V _{CC}	Fast



LOGIC DIAGRAM (POSITIVE LOGIC)(1)



(1) Pin numbers shown are for the DGG and DGV packages.



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Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT	
V _{CC} BIAS V _{CC}	Supply voltage range		-0.5	4.6	V	
V	Input valtage range (2)	A-port, ERC, and control inputs	-0.5	7	V	
V _I	Input voltage range ⁽²⁾	B port and V _{REF}	-0.5	4.6	V	
V	Voltage range applied to any output in the	A port	-0.5	7	V	
Vo	high-impedance or power-off state (2)	B port	-0.5	4.6	V	
	Owner that a second set in the Level state	A port		48	^	
l _o	Current into any output in the low state	B port		200	mA	
Io	Current into any A-port output in the high state	(3)		48	mA	
	Continuous current through each V _{CC} or GND			±100	mA	
I _{IK}	Input clamp current	V ₁ < 0		-50	mA	
I _{OK}	Output clamp current	V _O < 0		-50	mA	
		DGG package		64		
θ_{JA}	Package thermal impedance ⁽⁴⁾	DGV package		48	°C/W	
			42			
T _{stg}	Storage temperature range		-65	150	°C	

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

 ⁽²⁾ The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 (3) This current flows only when the output is in the high state and V_O > V_{CC}.
 (4) The package thermal impedance is calculated in accordance with JESD 51-7.



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Recommended Operating Conditions (1)(2)(3)(4)

			MIN	NOM	MAX	UNIT	
$V_{\rm CC}$, BIAS $V_{\rm CC}$	Supply voltage		3.15	3.3	3.45	V	
\/	Termination valtage	GTL	1.14	1.2	1.26	V	
V_{TT}	Termination voltage	GTLP	1.35	1.5	1.65	V	
W	Peferance valtage	GTL	0.74	8.0	0.87	V	
V_{REF}	Reference voltage	GTLP	0.87	1	1.1	V	
V	Input voltage	B port			V_{TT}	V	
V _I	Input voltage	Except B port		V_{CC}	5.5	V	
		B port	V _{REF} + 0.05				
V_{IH}	High-level input voltage	ERC	V _{CC} - 0.6	V_{CC}	5.5	V	
		Except B port and ERC	2				
		B port			$V_{REF} - 0.05$		
V_{IL}	Low-level input voltage	ERC	<u>ERC</u> GND		0.6	V	
		Except B port and ERC			0.8		
I _{IK}	Input clamp current				-18	mA	
I _{OH}	High-level output current	A port			-24	mA	
1	Low level output ourrent	A port			24	mA	
I _{OL}	Low-level output current	B port			100		
Δt/Δν	Input transition rise or fall rate	Outputs enabled			10	ns/V	
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		20			μs/V	
T _A	Operating free-air temperature		-40		85	°C	

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

Proper connection sequence for use of the B-port I/O precharge feature is GND and BIAS $V_{CC} = 3.3 \text{ V}$ first, I/O second, and $V_{CC} = 3.3 \text{ V}$ last, because the BIAS V_{CC} precharge circuitry is disabled when any V_{CC} pin is connected. The control and V_{REF} inputs can be connected anytime, but normally are connected during the I/O stage. If B-port precharge is not required, any connection sequence is acceptable but, generally, GND is connected first.

 V_{TT} and R_{TT} can be adjusted to accommodate backplane impedances if the dc recommended I_{OL} ratings are not exceeded. V_{REF} can be adjusted to optimize noise margins, but normally is two-thirds V_{TT} . TI-OPC circuitry is enabled in the A-to-B direction and is activated when $V_{TT} > 0.7$ V above V_{REF} . If operated in the A-to-B direction, V_{REF} should be set to within 0.6 V of V_{TT} to minimize current

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Electrical Characteristics

over recommended operating free-air temperature range for GTLP (unless otherwise noted)

P/	ARAMETER	TEST CONDITIONS		MIN	TYP ⁽¹⁾	MAX	UNIT		
V _{IK}		V _{CC} = 3.15 V,	$I_{I} = -18 \text{ mA}$			-1.2	V		
		V _{CC} = 3.15 V to 3.45 V,	$I_{OH} = -100 \mu A$	V _{CC} - 0.2					
V_{OH}	A port	V _{CC} = 3.15 V	I _{OH} = -12 mA	2.4			V		
		V _{CC} = 3.15 V	$I_{OH} = -24 \text{ mA}$	2					
		$V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	I_{OL} = 100 μ A			0.2			
	A port	V _{CC} = 3.15 V	$I_{OL} = 12 \text{ mA}$			0.4			
V		V _{CC} = 3.13 V	$I_{OL} = 24 \text{ mA}$			0.5	V		
V_{OL}			$I_{OL} = 10 \text{ mA}$			0.2	V		
	B port Control inputs	V _{CC} = 3.15 V	$I_{OL} = 64 \text{ mA}$			0.4			
			$I_{OL} = 100 \text{ mA}$			0.55			
I_{\parallel}	Control inputs	$V_{CC} = 3.45 \text{ V},$	$V_1 = 0 \text{ or } 5.5 \text{ V}$			±10	μΑ		
I _{OZH} ⁽²⁾	A port	V _{CC} = 3.45 V	$V_O = V_{CC}$			10	μА		
'OZH`	B port	V _{CC} = 3.43 V	V _O = 1.5 V			10	μΑ		
$I_{OZL}^{(2)}$	A and B ports	$V_{CC} = 3.45 \text{ V},$	$V_O = GND$			-10	μΑ		
I _{BHL} ⁽³⁾	A port	$V_{CC} = 3.15 \text{ V},$	$V_1 = 0.8 \ V$	75			μΑ		
I _{BHH} (4)	A port	$V_{CC} = 3.15 \text{ V},$	$V_I = 2 V$	-75			μΑ		
I _{BHLO} ⁽⁵⁾	A port	$V_{CC} = 3.45 \text{ V},$	$V_I = 0$ to V_{CC}	500			μΑ		
I _{BHHO} ⁽⁶⁾	A port	$V_{CC} = 3.45 \text{ V},$	$V_I = 0$ to V_{CC}	-500			μΑ		
		$V_{CC} = 3.45 \text{ V}, I_{C} = 0,$	Outputs high			40			
I_{CC}	A or B port	V_{I} (A-port or control inputs) = V_{CC} or GND,	Outputs low			40	mA		
		V_I (B port) = V_{TT} or GND	Outputs disabled			40			
ΔI _{CC} ⁽⁷⁾		V_{CC} = 3.45 V, One A-port or control input at V_{CC} – 0.6 V, Other A-port or control inputs at V_{CC} or GND				1.5	mA		
C _i	Control inputs	V _I = 3.15 V or 0			4	5	pF		
C	A port	V _O = 3.15 V or 0			6.5	7.5	pF		
C _{io}	B port	V _O = 1.5 V or 0	C _O = 1.5 V or 0				þΓ		

- (1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
 (2) For I/O ports, the parameters I_{OZH} and I_{OZL} include the input leakage current.
 (3) The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL}max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to V_{IL} max.
- The bus-hold circuit can source at least the minimum high sustaining current at V_{IH}min. I_{BHH} should be measured after raising V_{IN} to V_{CC} and then lowering it to $V_{IH}min$.
- An external driver must source at least I_{BHLO} to switch this node from low to high. An external driver must sink at least I_{BHHO} to switch this node from high to low.
- This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.

Hot-Insertion Specifications for A Port

over recommended operating free-air temperature range

PARAMETER		MIN	MAX	UNIT		
l _{off}	$V_{CC} = 0$,	BIAS $V_{CC} = 0$,	V_I or $V_O = 0$ to 5.5 V		10	μΑ
I _{OZPU}	$V_{CC} = 0 \text{ to } 1.5 \text{ V},$	$V_0 = 0.5 \text{ V to 3 V},$	OE = 0		±30	μΑ
I _{OZPD}	$V_{CC} = 1.5 \text{ V to } 0,$	$V_0 = 0.5 \text{ V to 3 V},$	OE = 0		±30	μΑ

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Live-Insertion Specifications for B Port

over recommended operating free-air temperature range

PARAMETER		TEST CONDITIONS							
I _{off}	$V_{CC} = 0$,	BIAS $V_{CC} = 0$,	V_I or $V_O = 0$ to 1.5 V		10	μΑ			
I _{OZPU}	$V_{CC} = 0 \text{ to } 1.5 \text{ V},$	BIAS $V_{CC} = 0$,	$V_O = 0.5 \text{ V to } 1.5 \text{ V}, \overline{OE} = 0$		±30	μΑ			
I _{OZPD}	$V_{CC} = 1.5 \text{ V to } 0,$	BIAS $V_{CC} = 0$,	$V_O = 0.5 \text{ V to } 1.5 \text{ V}, \overline{OE} = 0$		±30	μΑ			
I (DIACA)	$V_{CC} = 0 \text{ to } 3.15 \text{ V}$	BIAS V _{CC} = 3.15 V to 3.45 V,	V_0 (B port) = 0 to 1.5 V		5	mA			
I _{CC} (BIAS V _{CC})	$V_{CC} = 3.15 \text{ V to } 3.45 \text{ V}$	BIAS $V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	v _O (В роп) = 0 to 1.5 v		10	μΑ			
Vo	$V_{CC} = 0$,	BIAS $V_{CC} = 3.3 \text{ V}$,	$I_O = 0$	0.95	1.05	V			
Io	$V_{CC} = 0$,	BIAS $V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	V _O (B port) = 0.6 V	-1		μΑ			

Switching Characteristics

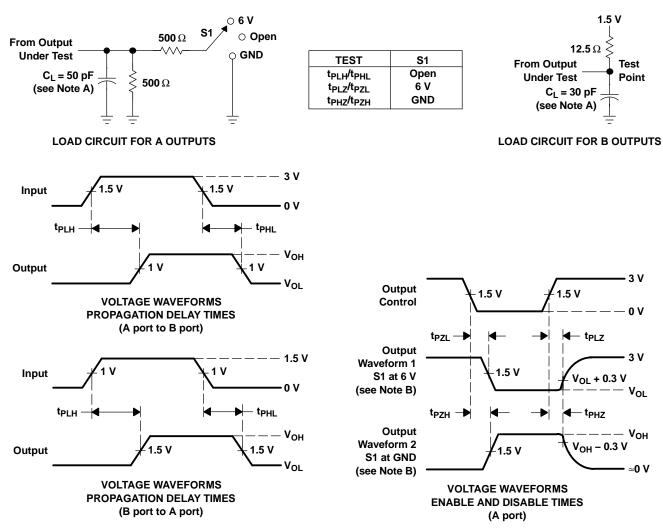
over recommended ranges of supply voltage and operating free-air temperature, $V_{TT} = 1.5 \text{ V}$ and $V_{REF} = 1 \text{ V}$ for GTLP (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE(1)	MIN	TYP ⁽²⁾	MAX	UNIT	
t _{PLH}	Α	В	Slow	3.9		7.2	20	
t _{PHL}	A	Б	Slow	3.1		8.4	ns	
t _{PLH}	Α	В	Fast	2.6		5.7	ns	
t _{PHL}	A	Ь	rasi	2.1		5.8	115	
t _{en}	ŌĒ	В	Slow	4.1		7.3	ns	
t _{dis}	OL	В	Slow	4		9.4	ns	
t _{en}	ŌĒ	В	Fast	2.9		5.9	ns	
t _{dis}	OE	Б		4		6.9		
•	Pico timo P outo	uts (20% to 80%)	Slow		3		ns	
t _r	Rise time, b outp	uis (20% to 60%)	Fast	1.5			115	
	Fall time P outpu	uts (80% to 20%)	Slow		4		20	
t _f	raii time, b outpo	uis (60% to 20%)	Fast	2.5		ns		
t _{PLH}	В	А		0.5		6.7	20	
t _{PHL}	ь	A		1.2		4.5	ns	
t _{en}	ŌĒ	A		1.1		6.3	nc	
t _{dis}	OE	A		1.7		5.1	ns	

Slow ($\overline{\text{ERC}}$ = GND) and Fast ($\overline{\text{ERC}}$ = V_{CC}) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.



PARAMETER MEASUREMENT INFORMATION



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \approx 10 MHz, $Z_O = 50 \Omega$, $t_r \approx 2$ ns, $t_f \approx 2$ ns.
 - D. The outputs are measured one at a time, with one transition per measurement.

Figure 1. Load Circuits and Voltage Waveforms

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Distributed-Load Backplane Switching Characteristics

The preceding switching characteristics table shows the switching characteristics of the device into a lumped load (Figure 1). However, the designer's backplane application probably is a distributed load. The physical representation is shown in Figure 2. This backplane, or distributed load, can be approximated closely to a resistor inductance capacitance (RLC) circuit, as shown in Figure 3. This device has been designed for optimum performance in this RLC circuit. The following switching characteristics table shows the switching characteristics of the device into the RLC load, to help the designer better understand the performance of the GTLP device in this typical backplane. See www.ti.com/sc/gtlp for more information.

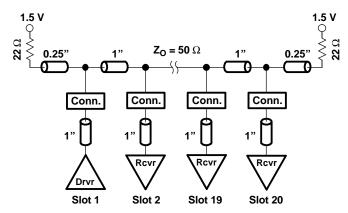


Figure 2. High-Drive Test Backplane

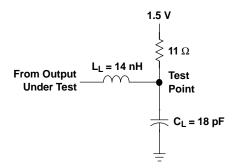


Figure 3. High-Drive RLC Network



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Switching Characteristics

over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE(1)	TYP ⁽²⁾	UNIT	
t _{PLH}	A	В	Slow	4.9	ns	
t _{PHL}	A	Ь	Slow	4.9		
t _{PLH}	А	В	Fast	3.7	ns	
t _{PHL}	A	В	rasi	3.7	115	
t _{en}	ŌĒ	В	Slow	5.1	ns	
t _{dis}	OL	В	Slow	5.4		
t _{en}	ŌĒ	В	Fast	4.1	ns	
t _{dis}	OL .	В	1 doi	4.1		
+	Pico timo P outr	oute (20% to 90%)	Slow	2	ns	
t _r	Rise time, b outp	outs (20% to 80%)	Fast	1.2		
4	Fall time. Plaute	uts (80% to 20%)	Slow	2.5	20	
t _f	raii time, b outp	uis (00% iu 20%)	Fast 1		ns	

⁽¹⁾ Slow (\overline{ERC} = GND) and Fast (\overline{ERC} = V_{CC}) (2) All typical values are at V_{CC} = 3.3 V, T_A = 25°C. All values are derived from TI-SPICE models.



PACKAGE OPTION ADDENDUM

10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
74GTLPH1645DGGRG4	ACTIVE	TSSOP	DGG	56	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	GTLPH1645	Samples
SN74GTLPH1645DGGR	ACTIVE	TSSOP	DGG	56	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	GTLPH1645	Samples
SN74GTLPH1645DGVR	ACTIVE	TVSOP	DGV	56	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	GL45	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

10-Dec-2020

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74GTLPH1645DGGR	TSSOP	DGG	56	2000	330.0	24.4	8.6	15.6	1.8	12.0	24.0	Q1
SN74GTLPH1645DGVR	TVSOP	DGV	56	2000	330.0	24.4	6.8	11.7	1.6	12.0	24.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins SPQ		Length (mm)	Width (mm)	Height (mm)	
SN74GTLPH1645DGGR	TSSOP	DGG	56	2000	367.0	367.0	45.0	
SN74GTLPH1645DGVR	TVSOP	DGV	56	2000	367.0	367.0	45.0	

DGV (R-PDSO-G**)

24 PINS SHOWN

PLASTIC SMALL-OUTLINE



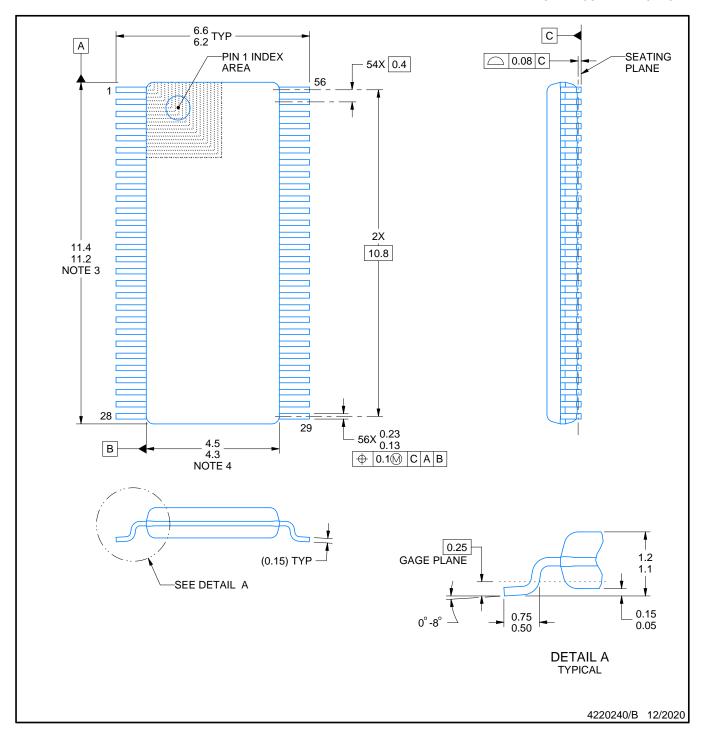
NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.

D. Falls within JEDEC: 24/48 Pins – MO-153 14/16/20/56 Pins – MO-194





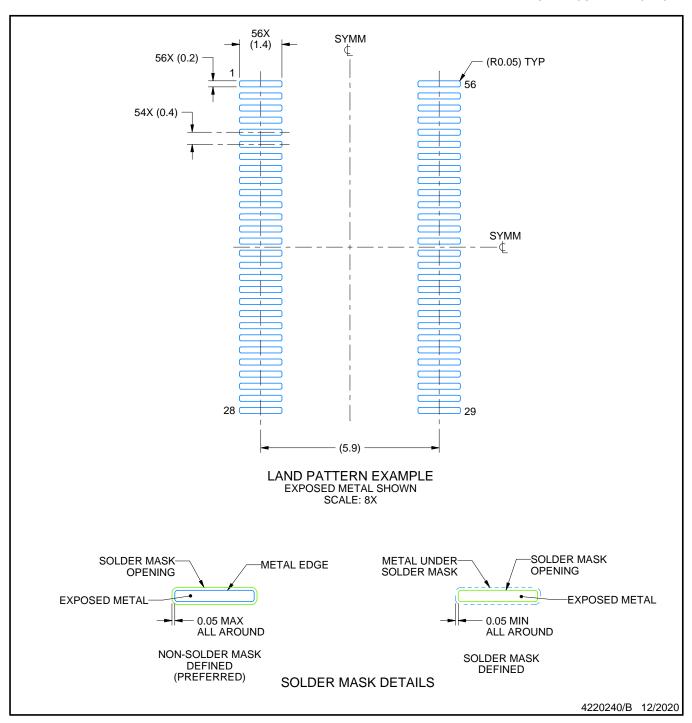
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-194.



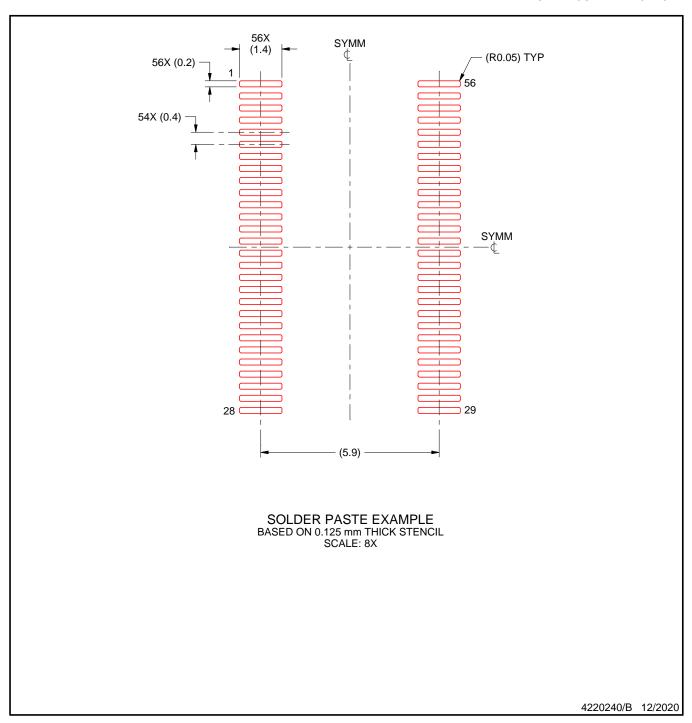


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-153.





NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



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